ALPHA & OMEGA SEMICONDUCTOR

AOD480

30V N-Channel MOSFET

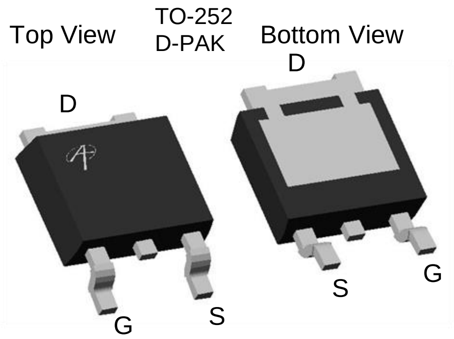
General Description

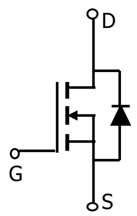
The AOD480 uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. This device is suitable for use in PWM, load switching and general purpose applications.

Features

V_{DS} (V) = 30V
I_D = 25A (V_{GS} = 10V)
$R_{DS(ON)}$ <23 mΩ (V_{GS} = 10V)
$R_{DS(ON)}$ <33 mΩ (V_{GS} = 4.5V)

100% UIS Tested
100% Rg Tested





Absolute Maximum Ratings T_A=25°C unless otherwise noted

Parameter		Symbol	Maximum	Units
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current [G]	T_C=25°C	I_D	25	A
	T_C=100°C		18	
Pulsed Drain Current [C]		I_{DM}	64	
Avalanche Current [C]		I_{AR}	12	A
Repetitive avalanche energy L=0.1mH [C]		E_{AR}	7	mJ
Power Dissipation [B]	T_C=25°C	P_D	21	W
	T_C=100°C		11	
Power Dissipation [A]	T_A=25°C	P_{DSM}	2.5	W
	T_A=70°C		1.6	
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 175	°C

Thermal Characteristics

Parameter		Symbol	Typ	Max	Units
Maximum Junction-to-Ambient [A]	t ≤ 10s	$R_{\theta JA}$	16.7	25	°C/W
Maximum Junction-to-Ambient [A]	Steady-State		40	50	°C/W
Maximum Junction-to-Case [B]	Steady-State	$R_{\theta JC}$	4.5	7	°C/W

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions		Min	Typ	Max	Units
STATIC PARAMETERS							
BV_{DSS}	Drain-Source Breakdown Voltage	I_D=250µA, V_{GS}=0V		30			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=24V, V_{GS}=0V			0.004	1	µA
			T_J=55°C			5	
I_{GSS}	Gate-Body leakage current	V_{DS}=0V, V_{GS}= ±20V				100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS} I_D=250µA		1.5	2.1	2.6	V
$I_{D(ON)}$	On state drain current	V_{GS}=10V, V_{DS}=5V		64			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V, I_D=20A			18.5	23	mΩ
			T_J=125°C		26	32	
		V_{GS}=4.5V, I_D=8A			25.4	33	mΩ
g_{FS}	Forward Transconductance	V_{DS}=5V, I_D=20A			20		S
V_{SD}	Diode Forward Voltage	I_S=1A,V_{GS}=0V			0.75	1	V
I_S	Maximum Body-Diode Continuous Current					3.2	A
DYNAMIC PARAMETERS							
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=15V, f=1MHz			373	448	pF
C_{oss}	Output Capacitance				67		pF
C_{rss}	Reverse Transfer Capacitance				41		pF
R_g	Gate resistance	V_{GS}=0V, V_{DS}=0V, f=1MHz			2	2.8	Ω
SWITCHING PARAMETERS							
Q_g(10V)	Total Gate Charge	V_{GS}=10V, V_{DS}=15V, I_D=20A		5.7	7.1	8.6	nC
Q_g(4.5V)	Total Gate Charge			2.7	3.5	4.2	nC
Q_{gs}	Gate Source Charge				1.2		nC
Q_{gd}	Gate Drain Charge				1.6		nC
$t_{D(on)}$	Turn-On DelayTime	V_{GS}=10V, V_{DS}=15V, R_L=0.75Ω, R_{GEN}=3Ω			4.3		ns
t_r	Turn-On Rise Time				2.8		ns
$t_{D(off)}$	Turn-Off DelayTime				15.8		ns
t_f	Turn-Off Fall Time				3		ns
t_{rr}	Body Diode Reverse Recovery Time	I_F=20A, dI/dt=100A/µs		8.4	10.5	12.6	ns
Q_{rr}	Body Diode Reverse Recovery Charge	I_F=20A, dI/dt=100A/µs		3.6	4.5	5.4	nC

A: The value of $R_{\theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A=25° C. The Power dissipation P_{DSM} is based on $R_{\theta JA}$ and the maximum allowed junction temperature of 150° C. The value in any given application depends on the user's specific board design, and the maximum temperature of 175° C may be used if the PCB allows it.
B. The power dissipation P_D is based on $T_{J(MAX)}$=175° C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.
C: Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$=175° C.
D. The $R_{\theta JA}$ is the sum of the thermal impedence from junction to case $R_{\theta JC}$ and case to ambient.
E. The static characteristics in Figures 1 to 6 are obtained using <300 µs pulses, duty cycle 0.5% max.
F. These curves are based on the junction-to-case thermal impedence which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of $T_{J(MAX)}$=175° C.
G. The maximum current is limited by package.
H. These tests are performed with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with T_A=25° C. The SOA curve provides a single pulse rating.
*This device is guaranteed green after data code 8X11 (Sep 1[ST] 2008).

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

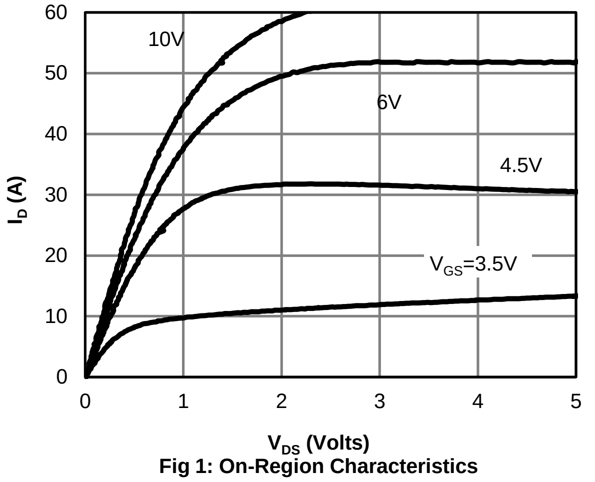


Fig 1: On-Region Characteristics

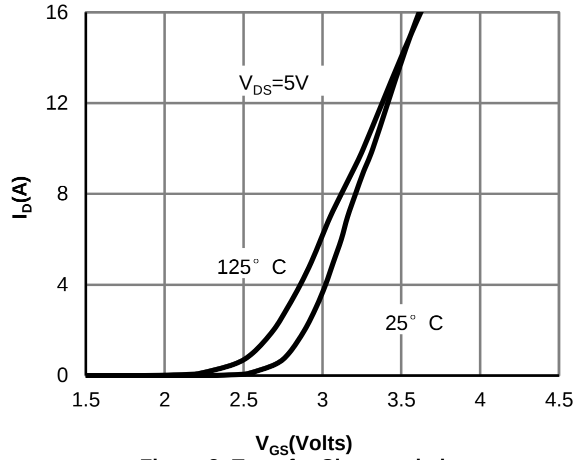


Figure 2: Transfer Characteristics

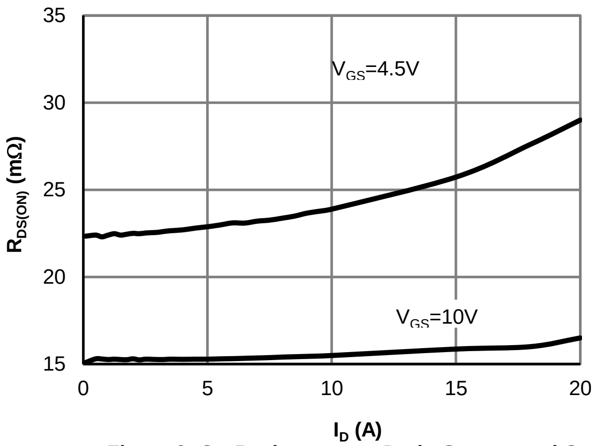


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

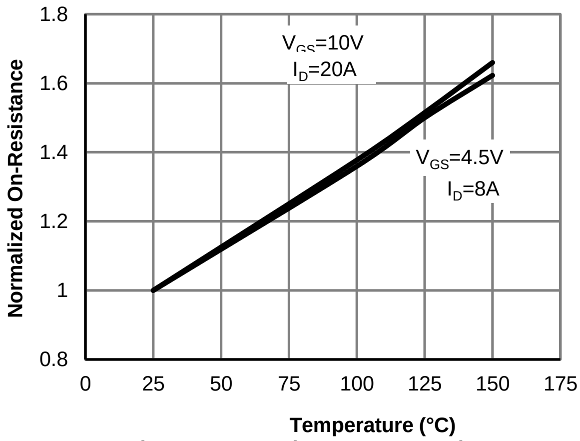


Figure 4: On-Resistance vs. Junction Temperature

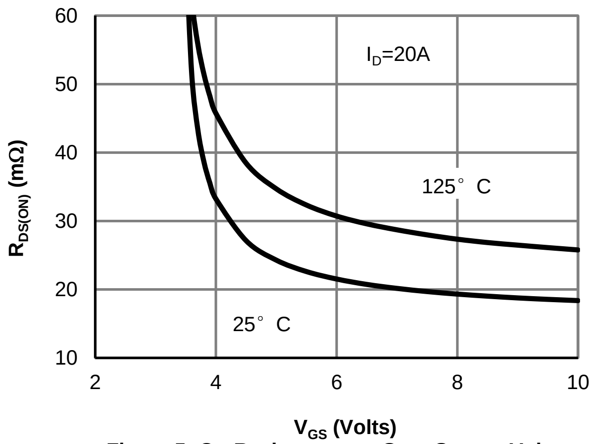


Figure 5: On-Resistance vs. Gate-Source Voltage

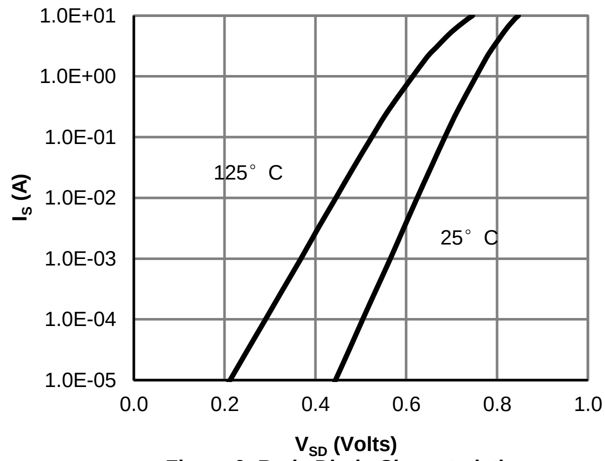


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

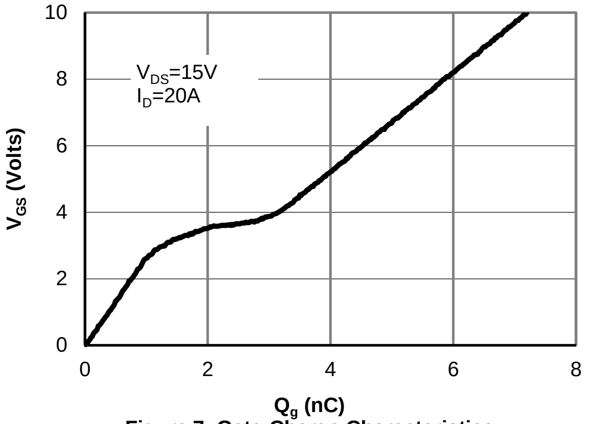


Figure 7: Gate-Charge Characteristics

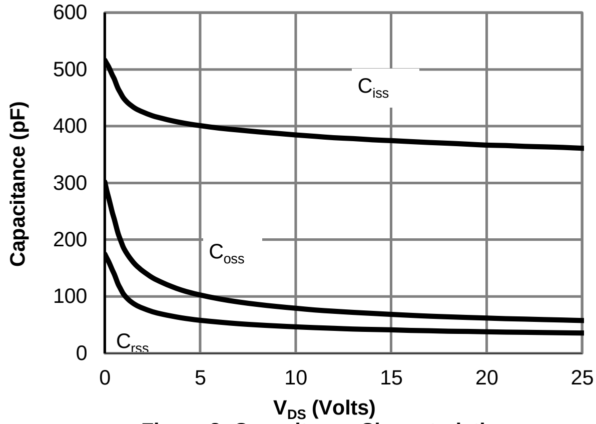


Figure 8: Capacitance Characteristics

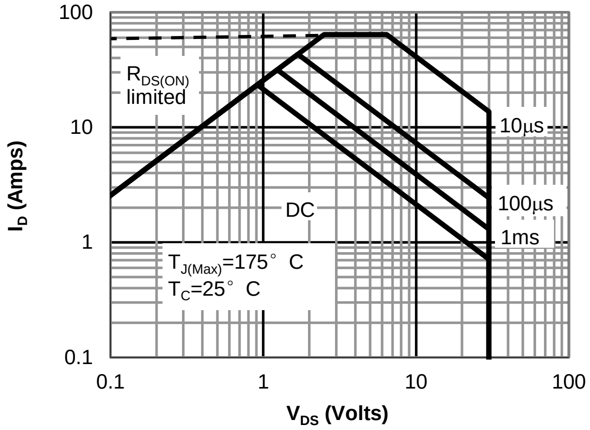


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

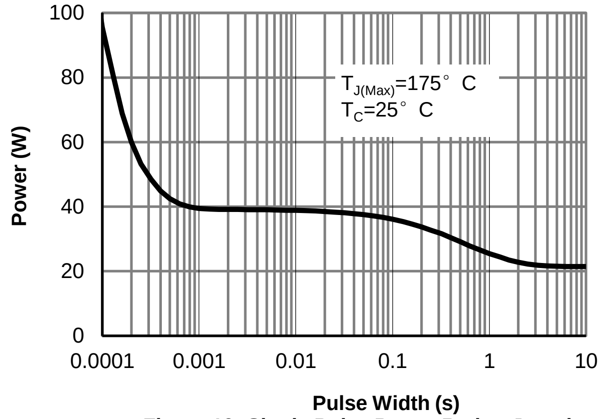


Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)

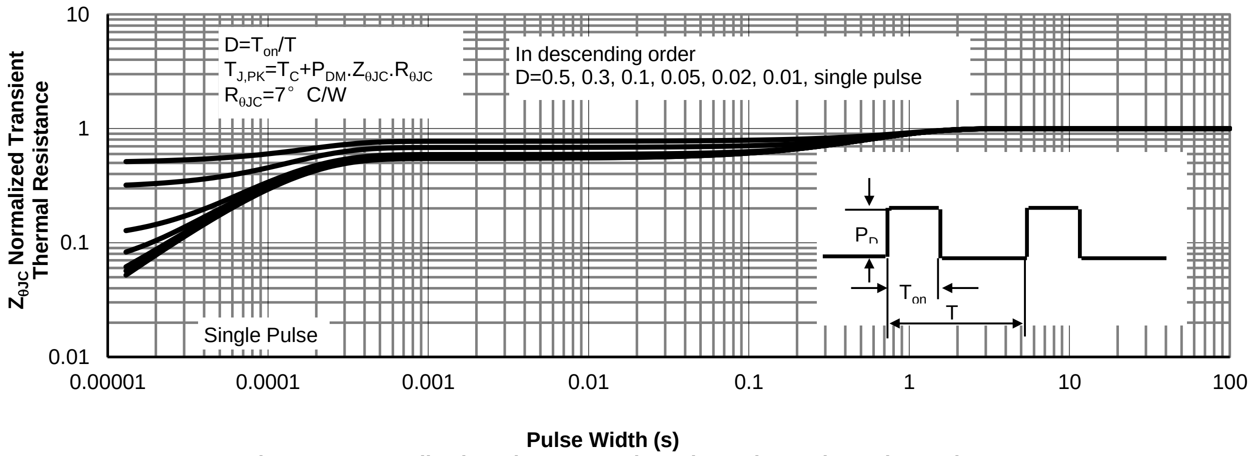


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

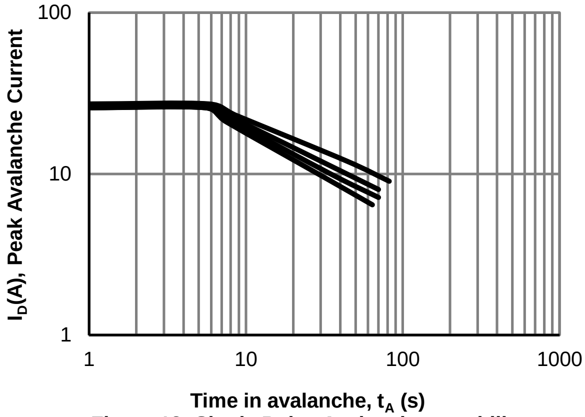


Figure 12: Single Pulse Avalanche capability

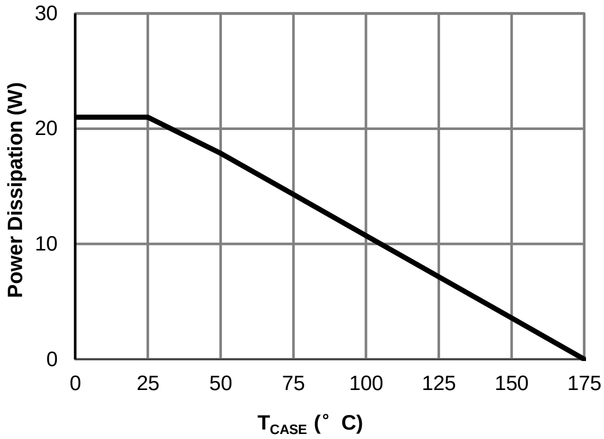


Figure 13: Power De-rating (Note B)

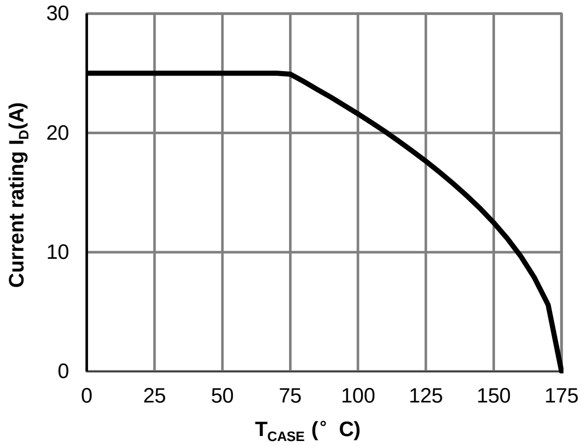


Figure 14: Current De-rating (Note B)

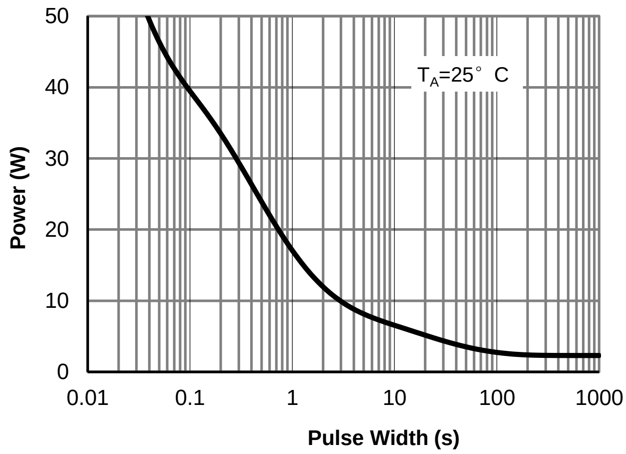


Figure 15: Single Pulse Power Rating Junction-to-Ambient (Note H)

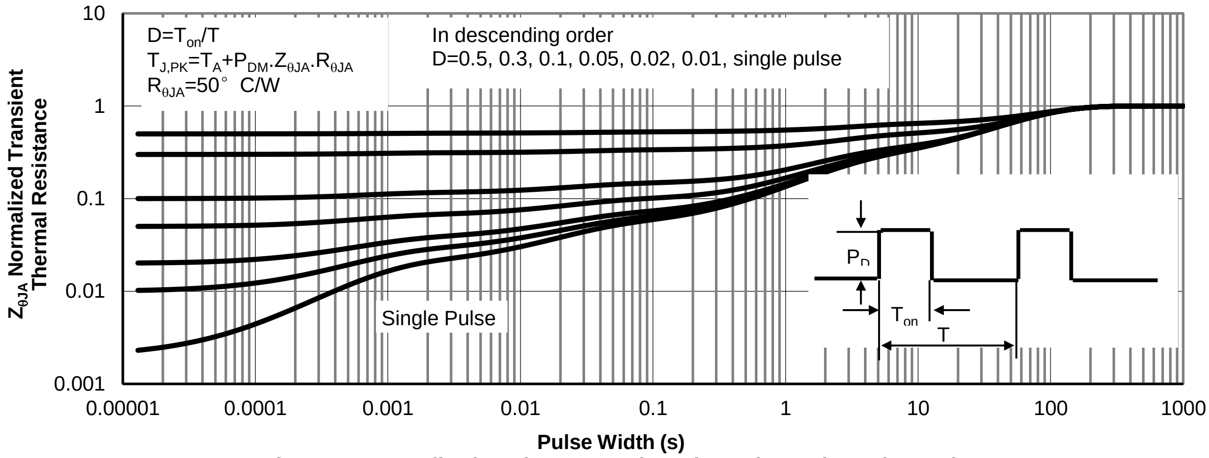
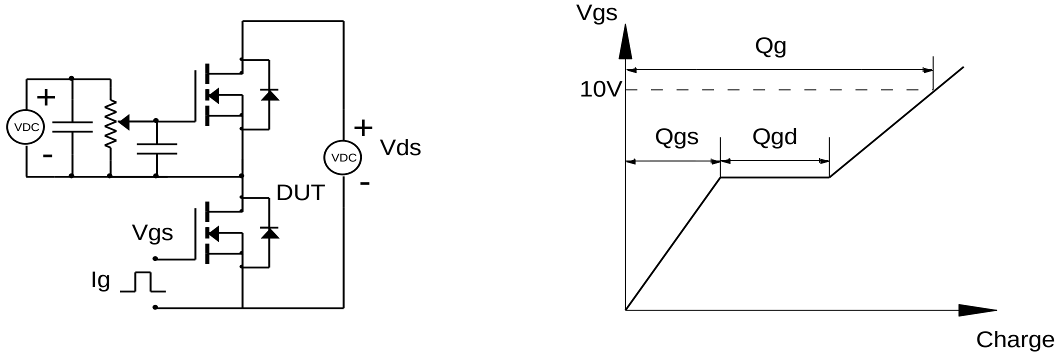
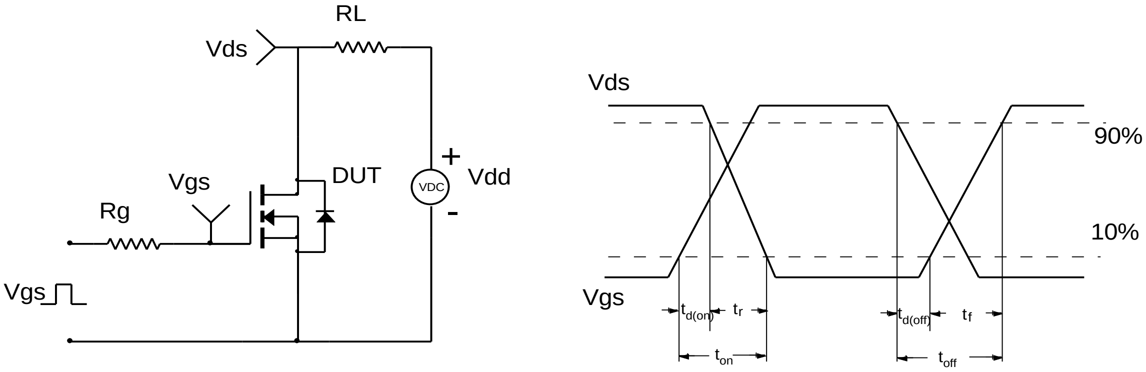


Figure 16: Normalized Maximum Transient Thermal Impedance (Note H)

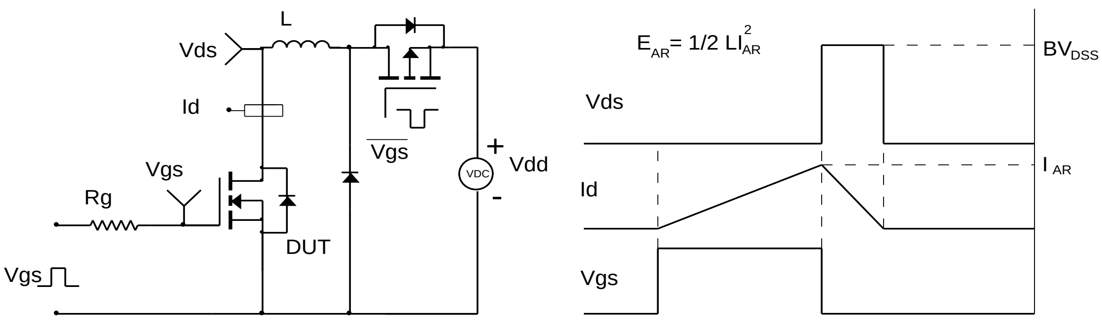
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms